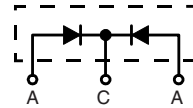


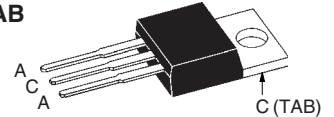
Power Schottky Rectifier with common cathode

$$\begin{aligned} I_{FAV} &= 2 \times 8 \text{ A} \\ V_{RRM} &= 100 \text{ V} \\ V_F &= 0.63 \text{ V} \end{aligned}$$

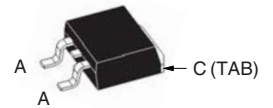
V_{RSM} V	V_{RRM} V	Type
100	100	DSSK 16-01A
100	100	DSSK 16-01AS



TO-220 AB
(A-Type)



TO-263 AB
(AS-Type)



A = Anode, C = Cathode, TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I_{FRMS}		35	A
I_{FAV}	$T_C = 165^\circ\text{C}$; rectangular, $d = 0.5$	8	A
I_{FAV}	$T_C = 165^\circ\text{C}$; rectangular, $d = 0.5$; per device	16	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t_p = 10 \text{ ms}$ (50 Hz), sine	120	A
E_{AS}	$I_{AS} = 5 \text{ A}$; $L = 100 \mu\text{H}$; $T_{VJ} = 25^\circ\text{C}$; non repetitive	1.3	mJ
I_{AR}	$V_A = 1.5 \cdot V_{RRM}$ typ.; $f = 10 \text{ kHz}$; repetitive	0.8	A
$(dv/dt)_{cr}$		5000	V/ μs
T_{VJ}		-55...+175	$^\circ\text{C}$
T_{VJM}		175	$^\circ\text{C}$
T_{stg}		-55...+150	$^\circ\text{C}$
P_{tot}	$T_C = 25^\circ\text{C}$	90	W
M_d	mounting torque (Version A only)	0.4...0.6	Nm
Weight	typical	2	g

Features

- International standard package
- Very low V_F
- Extremely low switching losses
- Low I_{RM} -values
- Epoxy meets UL 94V-0

Applications

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Dimensions see Outlines.pdf

Symbol	Conditions	Characteristic Values	
		typ.	max.
I_R ①	$V_R = V_{RRM}$; $T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$; $T_{VJ} = 125^\circ\text{C}$	0.3 2.5	mA mA
V_F	$I_F = 8 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$ $I_F = 8 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$ $I_F = 16 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$	0.63 0.81 0.75	V V V
R_{thJC} R_{thCH} (Version A only)	0.5	1.7	K/W K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified.

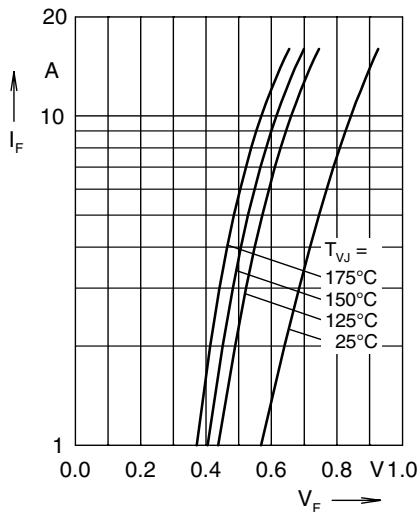


Fig. 1 Max. forward voltage drop characteristics

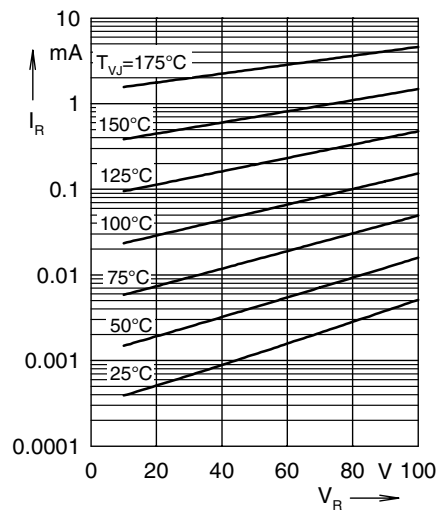


Fig. 2 Typ. reverse current I_R versus reverse voltage

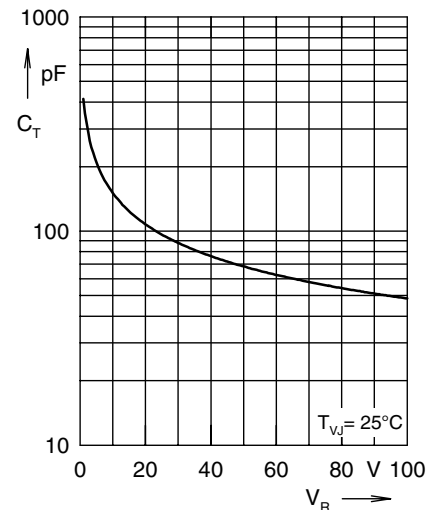


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

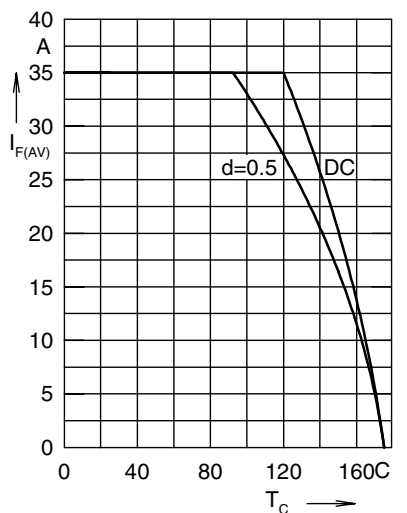


Fig. 4 Avg. forward current $I_{F(AV)}$ vs. case temperature T_C

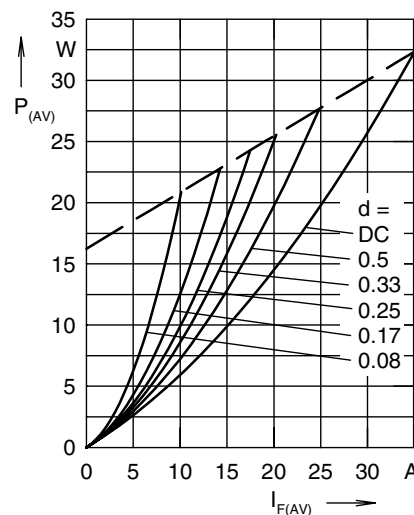


Fig. 5 Forward power loss characteristics

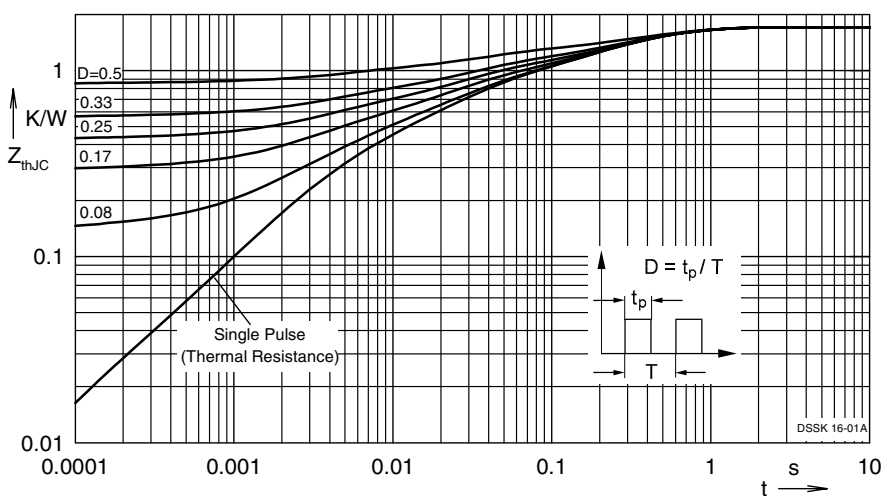


Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per Diode